60V N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
60V	69mΩ @ V_{GS} = 10V	14A
	100mΩ @ V_{GS} = 4.5V	12A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Power-management functions
- DC-DC converters

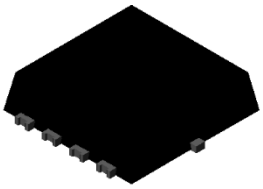
Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low $R_{DS(ON)}$ — Ensures Minimal On-State Losses
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspections
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN6069SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

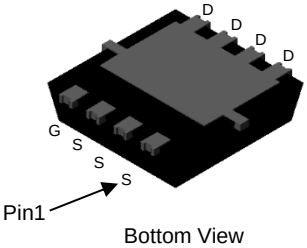
Mechanical Data

- Package: PowerDI®3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.029 grams (Approximate)

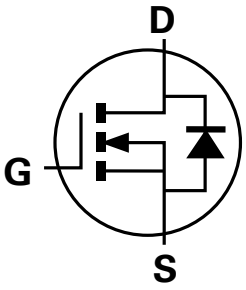
PowerDI3333-8/SWP (Type UX)



Top View



Bottom View



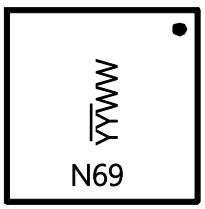
Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN6069SFVWQ-7	PowerDI3333-8/SWP (Type UX)	2,000	Tape & Reel
DMN6069SFVWQ-13	PowerDI3333-8/SWP (Type UX)	3,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



N69 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 25 = 2025)
WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 5)	Steady State	T_A = +25°C T_A = +70°C	I_D	4.0 3.2	A
Continuous Drain Current, V_{GS} = 10V (Note 6)	Steady State	T_C = +25°C T_C = +70°C	I_D	14 11	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	56	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	4.0	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	56	A
Avalanche Current, L = 0.1mH			I_{AS}	12	A
Repetitive Avalanche Energy, L = 0.1mH			E_{AS}	7.2	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	50	°C/W
Total Power Dissipation (Note 6)		P_D	32	W
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	3.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	35	69	mΩ	V_{GS} = 10V, I_D = 3A
		—	41	100		V_{GS} = 4.5V, I_D = 2.4A
Diode Forward Voltage	V_{SD}	—	0.8	1.1	V	V_{GS} = 0V, I_S = 2.5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	740	—	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	40	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	28	—	pF	
Gate Resistance	R_g	—	2.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.4	—	nC	V_{DS} = 30V, I_D = 12A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	14	—	nC	
Gate-Source Charge	Q_{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.3	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.6	—	ns	V_{DS} = 30V, I_D = 12A V_{GS} = 10V, R_G = 6.0Ω
Turn-On Rise Time	t_R	—	5.0	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	12	—	ns	
Turn-Off Fall Time	t_F	—	3.3	—	ns	
Body Diode Reverse-Recovery Time	t_{RR}	—	11	—	ns	I_F = 4.5A, di/dt = 100A/µs
Body Diode Reverse-Recovery Charge	Q_{RR}	—	5.1	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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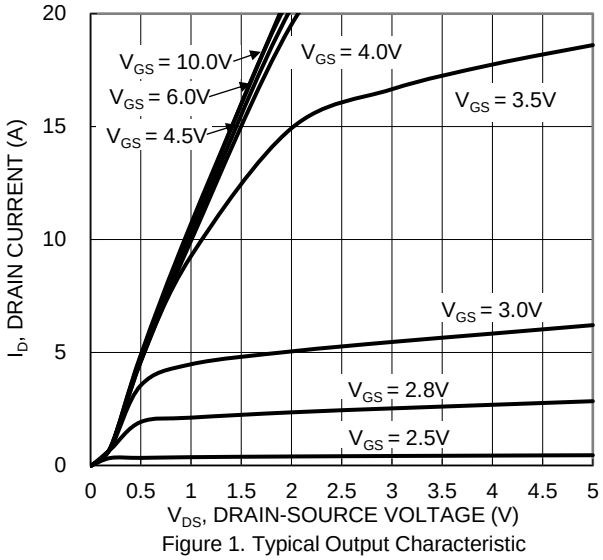


Figure 1. Typical Output Characteristic

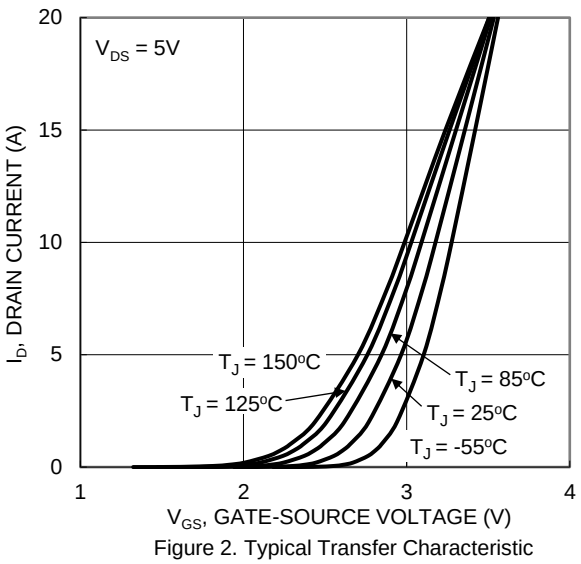


Figure 2. Typical Transfer Characteristic

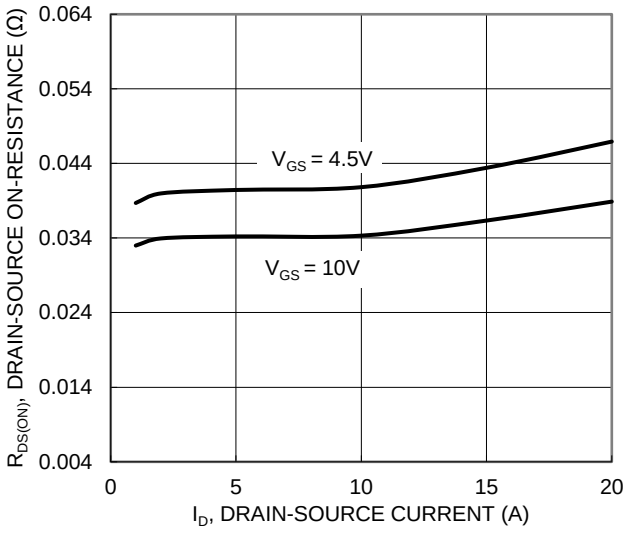


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

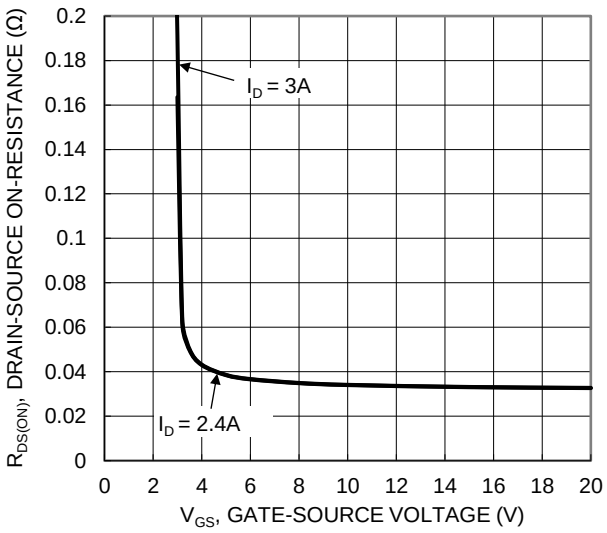


Figure 4. Typical Transfer Characteristic

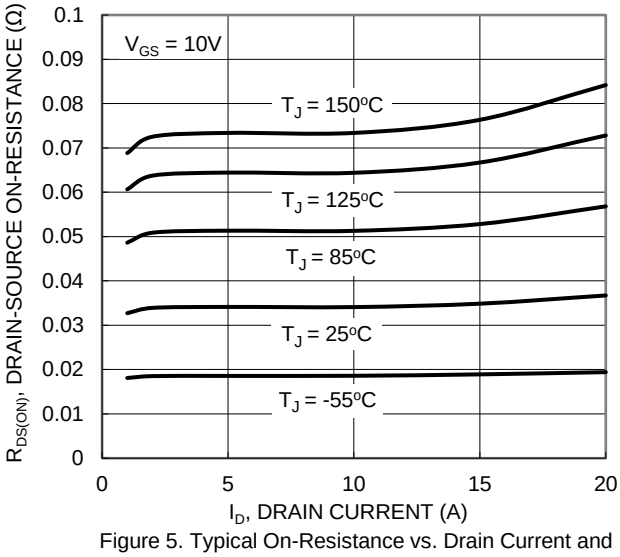


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

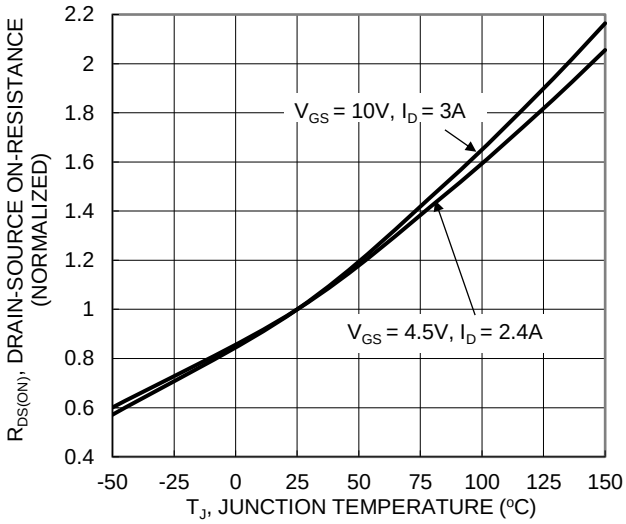


Figure 6. On-Resistance Variation with Junction Temperature

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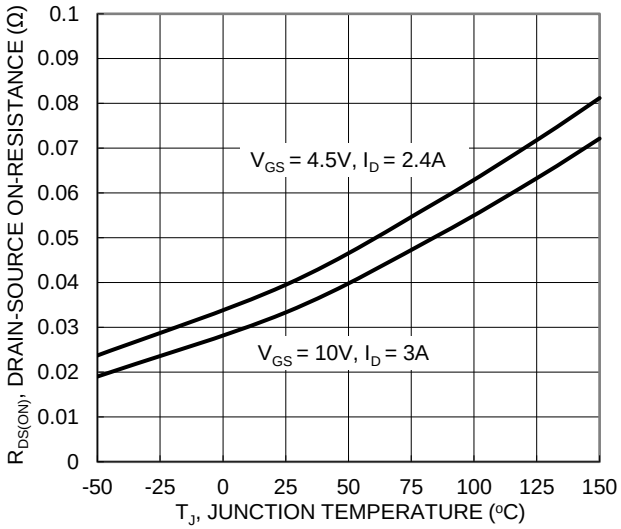


Figure 7. On-Resistance Variation with Junction Temperature

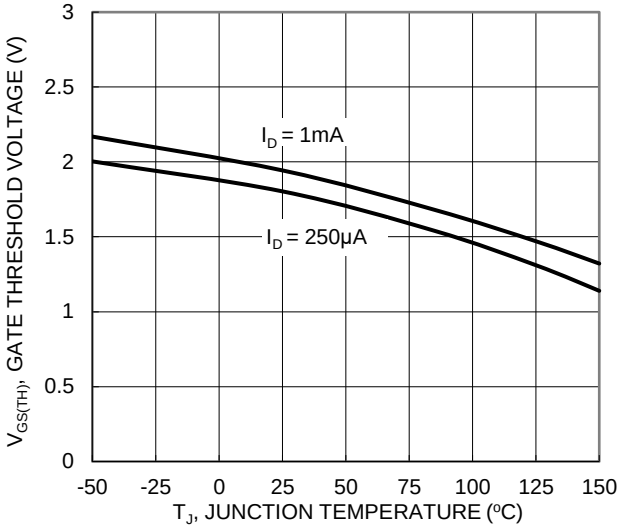


Figure 8. Gate Threshold Variation vs. Junction Temperature

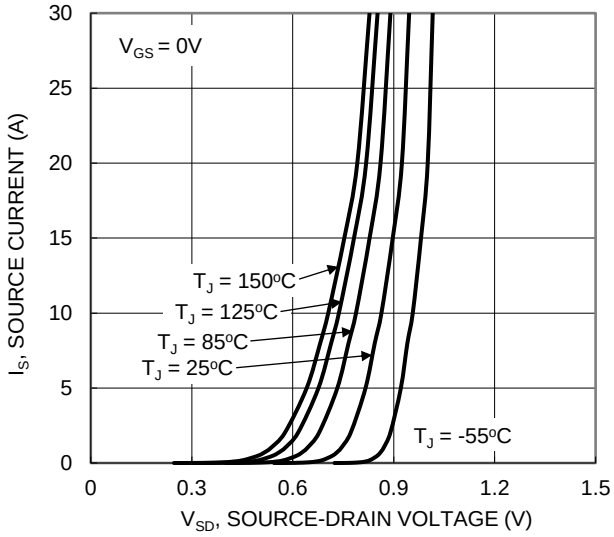


Figure 9. Diode Forward Voltage vs. Current

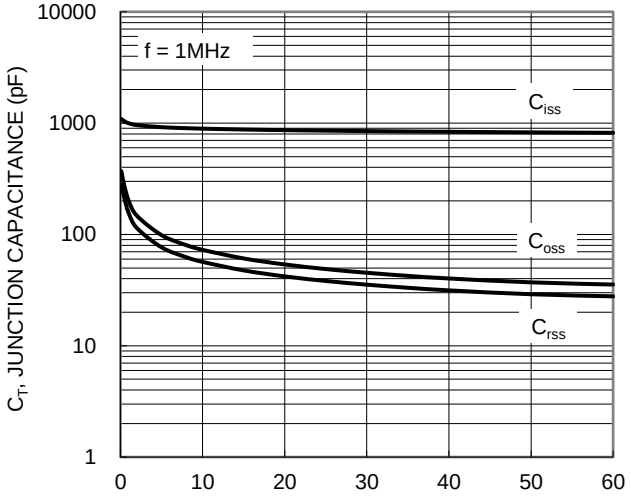


Figure 10. Typical Junction Capacitance

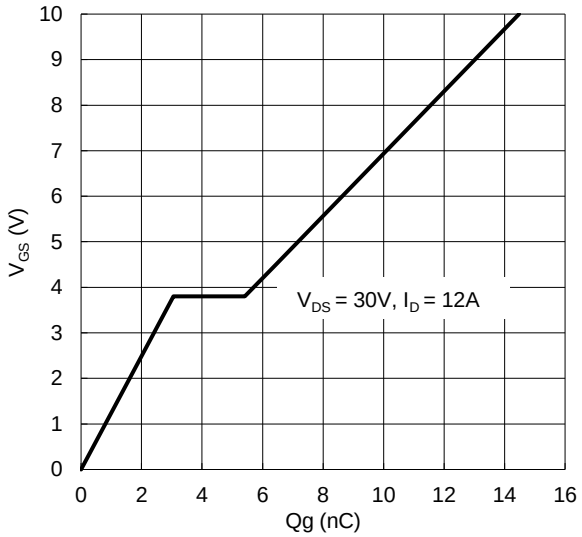


Figure 11. Gate Charge

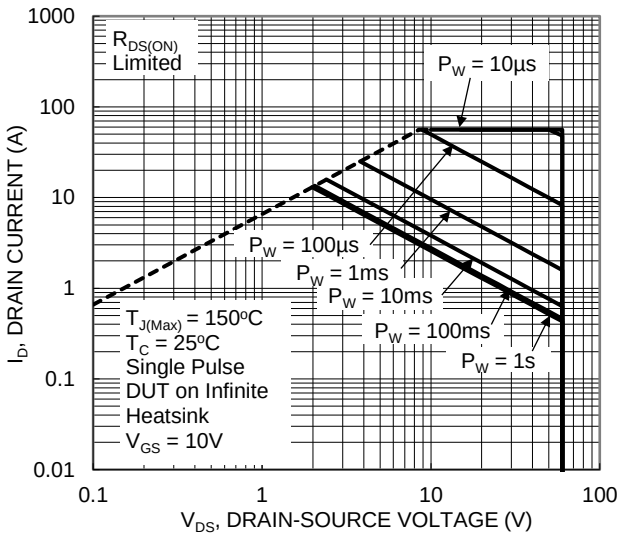


Figure 12. SOA, Safe Operation Area

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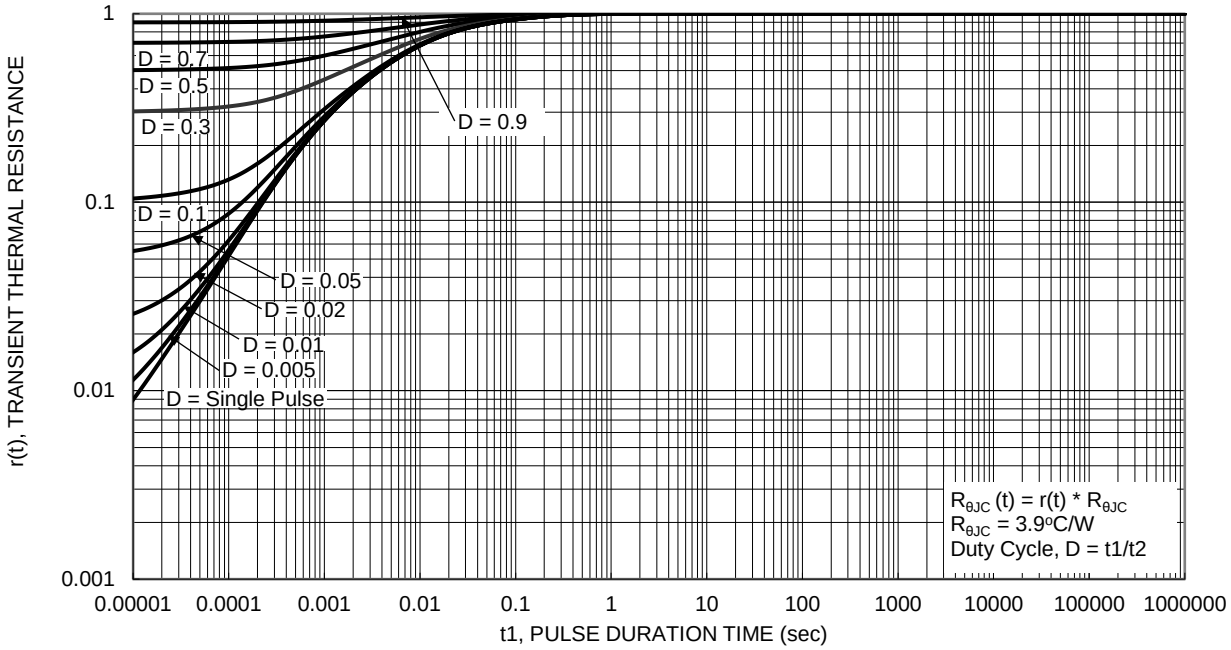


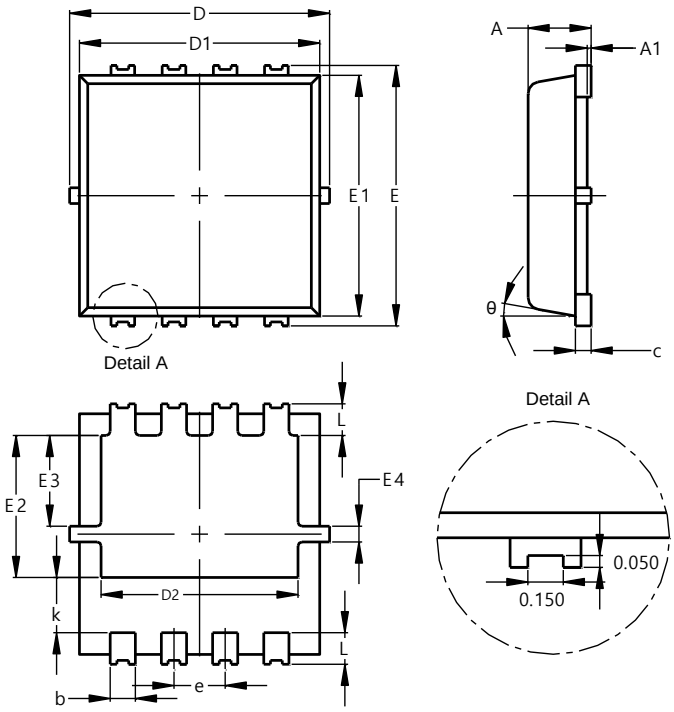
Figure 13. Transient Thermal Resistance

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)

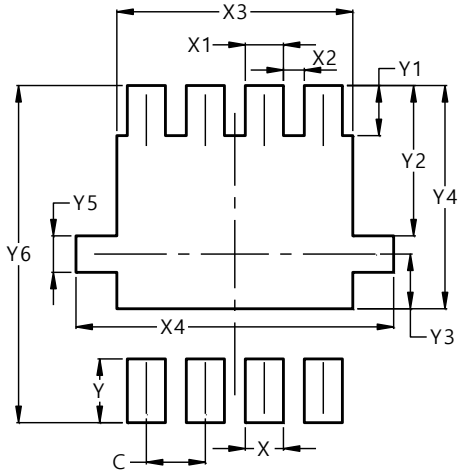


PowerDI3333-8/SWP (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	–	–	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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